

### **General Description**

The WSD4038DN is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSD4038DN meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

#### **Features**

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

### **Product Summery**

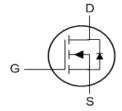
BVDSS	RDSON	ID
40V	13mΩ	38A

## **Applications**

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

### **DFN3.3X3.3-EP Pin Configuration**





### **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	40	V
$V_{GS}$	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>C</sub> =25℃	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	38	Α
I <sub>D</sub> @T <sub>C</sub> =100℃	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	20	Α
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	15	Α
I <sub>D</sub> @T <sub>A</sub> =70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	10	Α
I <sub>DM</sub> @Тс=25°С	Pulsed Drain Current <sup>2</sup>	36	Α
EAS	Avalanche Energy ,Single Pulse (L=0.1mH) <sup>3</sup>	26	mJ
I <sub>AS</sub>	Avalanche Current ,Single pulse(L=0.1mH) <sup>3</sup>	36	Α
P <sub>D</sub> @T <sub>A</sub> =25℃ Total Power Dissipation <sup>4</sup>		2.1	W
P <sub>D</sub> @T <sub>A</sub> =70°C	P <sub>D</sub> @T <sub>A</sub> =70 °C Total Power Dissipation <sup>4</sup>		W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	$^{\circ}$
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	${\mathbb C}$

#### **Thermal Data**

Symbol Parameter		Тур.	Max.	Unit
$R_{ heta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>		60	°C/W
R <sub>θJC</sub> Thermal Resistance Junction-Case <sup>1</sup>			2.1	°C/W



# Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	40			V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V , I <sub>D</sub> =7A		10.5	13	mΩ
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =4.5V , I <sub>D</sub> =5A		12	16	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.5	1.8	2.5	V
$\triangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	V <sub>GS</sub> -V <sub>DS</sub> , I <sub>D</sub> -230uA		-6.		mV/℃
I <sub>DSS</sub>	Drain-Source Leakage Current	$V_{DS}$ =32V , $V_{GS}$ =0V , $T_J$ =25 $^{\circ}$ C		-	2	uA
אטי	Diani-Source Leakage Guirent	$V_{DS}$ =32V , $V_{GS}$ =0V , $T_J$ =55 $^{\circ}\mathrm{C}$		-	10	u <sub>A</sub>
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}$ = $\pm20V$ , $V_{DS}$ = $0V$		-	±100	nA
gfs	orward Transconductance	$V_{DS}$ =5V , $I_D$ =20A		31		S
$R_g$	Gate Resistance	$V_{DS}$ =0V , $V_{GS}$ =0V , f=1MHz		1.1	1.8	Ω
$Q_g$	Total Gate Charge (10V)			20	28	
$Q_{gs}$	Gate-Source Charge	VDS=20V, VGS=10V, IDS=7A		3.9	7.5	nC
$Q_gd$	Gate-Drain Charge			3.0	5.1	
$T_{d(on)}$	Turn-On Delay Time	VDD=20V, RL=20		12.6	16	
Tr	Rise Time	3, IDS=1A, VGEN=10V,		10	12	ns
$T_{d(off)}$	Turn-Off Delay Time	RG=1Ω.		23.6	32	115
T <sub>f</sub>	Fall Time			6	9	
C <sub>iss</sub>	Input Capacitance			1125		
Coss	Output Capacitance	V <sub>DS</sub> =20V , V <sub>GS</sub> =0V , f=1MHz		132		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			70		

### **Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			5	Α
I <sub>SM</sub>	Pulsed Source Current <sup>2,6</sup>	VG-VD-UV, FOICE Current		-	15	Α
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =20A , T <sub>J</sub> =25℃		-	1.1	V

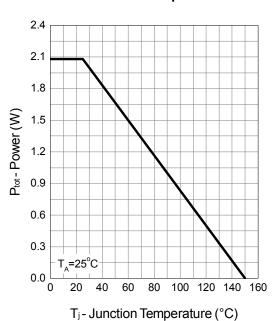
#### Note

- 1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper,t<10sec .
- 2.The data tested by pulsed , pulse width  $\leq$  300us , duty cycle  $\leq$  2%
- 3. The EAS data shows Max. rating . The test condition is  $V_{DD}$ =25V,  $V_{GS}$ =10V,L=0.5mH,  $I_{AS}$ =13A
- 4. The power dissipation is limited by 150 °C junction temperature
- 5. The Min. value is 100% EAS tested guarantee.
- 6. The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.
- 7. Package limitation current is 60A.

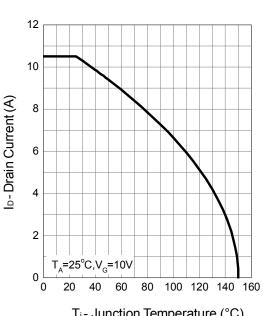


# **Typical Operating Characteristics**

# **Power Dissipation**

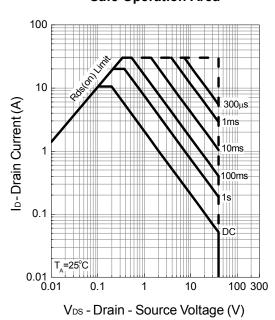


### **Drain Current**

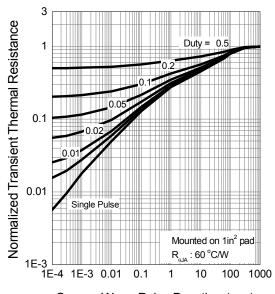


T<sub>j</sub>- Junction Temperature (°C)

## Safe Operation Area



### **Thermal Transient Impedance**

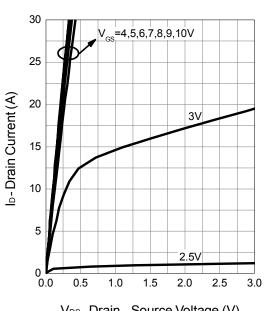


Square Wave Pulse Duration (sec)



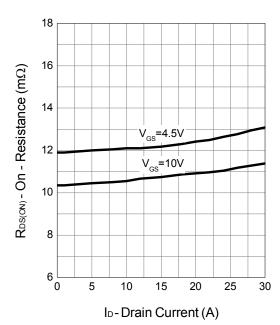
# **Typical Operating Characteristics (Cont.)**

# **Output Characteristics**

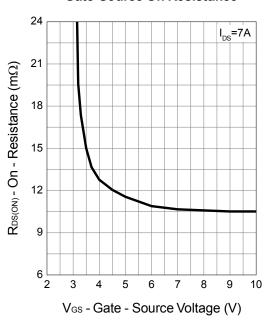


V<sub>DS</sub> - Drain - Source Voltage (V)

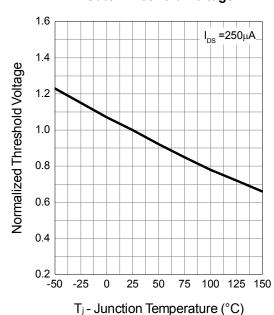
### **Drain-Source On Resistance**



### **Gate-Source On Resistance**



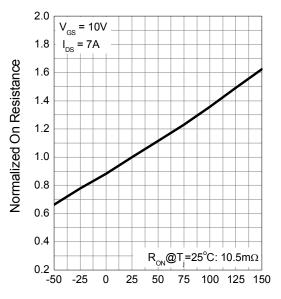
### **Gate Threshold Voltage**





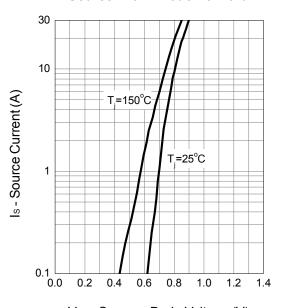
# **Typical Operating Characteristics (Cont.)**

# **Drain-Source On Resistance**



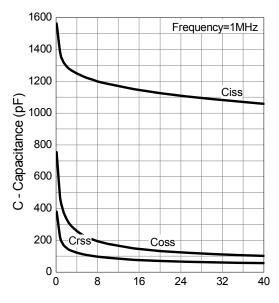
T<sub>j</sub> - Junction Temperature (°C)

#### Source-Drain Diode Forward



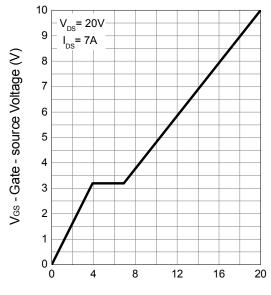
VsD - Source - Drain Voltage (V)

### Capacitance



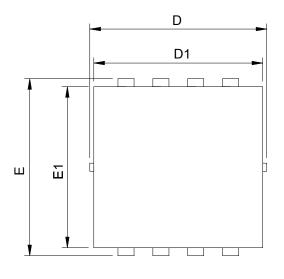
V<sub>DS</sub> - Drain - Source Voltage (V)

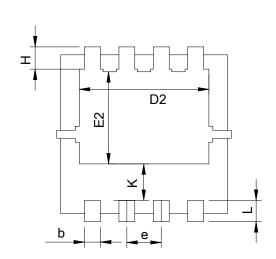
### **Gate Charge**



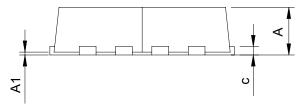
Q<sub>G</sub> - Gate Charge (nC)







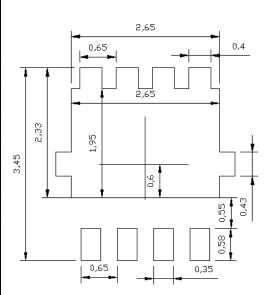
**Top View** 



**Bottom View** 

# **Side View**

S		DFN3.3x3.3	_EP		
SYMBOL	MILLIMETERS		INCHES		
6	MIN.	MAX.	MIN.	MAX.	
Α	0.70	1.00	0.028	0.039	
A1	0.00	0.05	0.000	0.002	
b	0.25	0.35	0.010	0.014	
С	0.14	0.20	0.006	0.008	
D	3.10	3.50	0.122	0.138	
D1	3.05	3.25	0.120	0.128	
D2	2.35	2.55	0.093	0.100	
E	3.10	3.50	0.122	0.138	
E1	2.90	3.10	0.114	0.122	
E2	1.64	1.84	0.065	0.072	
е	0.65 BSC		0.026	BSC	
Н	0.32	0.52	0.013	0.020	
K	0.59	0.79	0.023	0.031	
L	0.25	0.55	0.010	0.022	



UNIT: mm



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